

# TiO<sub>2</sub> nanoparticles impacts over color deviation in white light-emitting diodes

Thanh Binh Ly<sup>1</sup>, Nguyen Doan Quoc Anh<sup>2</sup>, Phan Xuan Le<sup>3</sup>

<sup>1</sup>Faculty of Fundamental Science, Industrial University of Ho Chi Minh City, Ho Chi Minh City, Vietnam

<sup>2</sup>Faculty of Electrical and Electronics Engineering, Ton Duc Thang University, Ho Chi Minh City, Vietnam

<sup>3</sup>Faculty of Mechanical-Electrical and Computer Engineering, School of Engineering and Technology, Van Lang University, Ho Chi Minh City, Vietnam

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## ABSTRACT

The effects of injecting TiO<sub>2</sub> nanoparticles with phosphorus silicone packing on white color light-emitting diodes (WLEDs) are examined. In WLED packages, the proposed approach may increase luminance emission by 2.7%, while the coordinated color temperature will increase by 39%. At the same time, the required phosphorus quantity will be lowered by 5% along with the joint temperature of 6.5 °C. The modifications, which boost illuminating performance and also reduce temperature aggregation, are because of the packing material's increased illuminating dispersion efficiency or even refracting indices, along with lower illuminating reduction, for which color fusing inside the parcels is responsible. Consequently, the results suggest improved WLED lighting system performance makes the products more appropriate in solid-state lighting.

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## Corresponding Author:

Phan Xuan Le

Faculty of Mechanical-Electrical and Computer Engineering, School of Engineering and Technology

Van Lang University

Ho Chi Minh City, Vietnam

Email: le.px@vlu.edu.vn

## 1. INTRODUCTION

Light-emitting diodes (LEDs), which is an abbreviation for light-emitting diodes, are manufactured from mixing blue-emitted LED chips and yellow emitting phosphorus layers are potential upcoming illumination contributors because of numerous advantages on incandescent and fluorescent lighting outlets, including their environmental friendliness, high energy efficiency, great reliability, good perceptible performance, as well as extended longevity. As a result, the bad luminous extracting efficacy (LEE) of GaN-based LEDs limits their usefulness [1]-[3]. Moreover, such condition of GaN is mainly resulted from the complete inner reflecting process around the LED's borders capturing illumination while LED chips' refracting indices are high. In addition, during the assembly phase, an LED chip is coated with one packaging film. The encapsulating substance in an LED packet easily reflects and absorbs the lighting. Regardless of a variety of testing in minimizing illuminating deficit, including enhancing the LED chip's exteriority structure [4]-[6], using reflecting cavity designs on LED leading structures [7], optimizing the packaging's components [8], as well as advancing the lens design [9], the large refracting indice variation around the LED chip/air borders remains a problem [10]-[13]. While employed as a solid-state illuminating supply, an LED must therefore be capable of creating bright white-emitting illumination with an affordable cost. Freestanding diffused distribution technique is the standard method of producing white-emitted LEDs. Such approach is insufficient to create excellent white-emitted LEDs, notably regarding better brightness and color uniformity

efficiency, because of high refracting indice difference around the LED chip/air borders and mismatch among the blue-emitted and yellow-emitted illuminations [14]-[16]. In the evaluation of WLEDs performance, the most important elements to examine are luminous extracting efficacy, color imbalance. Chip's exterior patterns [17], remote phosphorus structure [18], conformal phosphorus structure [19], reflecting cup pattern [20], phosphorus geometrical layout [21], scattered effect modelling [22], and silicon microparticles [23] are among the most recent suggestions to improve LED illumination qualities demonstrated in prior studies. Despite the fact that such research has improved white LED performance to many extends, this has yet to led to a full rise towards LED packing.  $\text{TiO}_2$  nano-particles (NPs) have excellent illumination dispersing capacity in sucessfully enhancing WLEDs performance and the refractive indices of packaging mediums [24]. This examination looks into the optical thermo characteristics of WLEDs made with varied quantities of  $\text{TiO}_2$  (NPs) and a silicon packaging phosphor. The proposed method is simple as it exploits current technology for producing low-cost commercial WLEDs and avoiding altering package optics or including additional optical elements. One requirement is that  $\text{TiO}_2$  and phosphorus concentrations be properly managed. In comparison to a traditional arrangement, with the exception of  $\text{TiO}_2$  injection on the similar correlated chromaticity temperature (CCT) level, experiments show that  $\text{TiO}_2$ -doped phosphorus silicon packaging promotes luminance creation, CCT distributed uniformity, and associated thermal features, and also reduces the number of phosphorus used in LED manufacturing, saving the expense.

## 2. EXPERIMENT

Commercialized  $\text{TiO}_2$  (NPs) and WLED packaging composites were developed, that would not filter illumination whose wavelengths of over 400 nm of visible band. As LED samples, commercialized GaN-based blue color LED with 1 mm chips (350 mA rated current) and 450 nm emitting wavelengths were used to attach to the commercialized plastics exteriority installation device center leading-structure (diameters in mm:  $6.5 \times 5 \times 0.9$ ) employing silvery mixture. To establish electrical connections between the LED chips with the leading structure, a cable binding process using gold cables has been employed. Figure 1 shows the wireframe designs for various LED structures, see Figure 1(a) and Figure 1(b). In blue-emitted LED chips featuring the same properties, various amounts of  $\text{TiO}_2$  and YAG phosphor with particle sizes of 21 mm and 8 mm, and including silicon packaging of the same 5600 K CCT, were used. The concentrations of  $\text{TiO}_2$ /phosphorus fine grains mixed in the standard phosphorus and  $\text{TiO}_2$ -doped phosphorus solutions were 0/6 and 0.02/5.7 wt.%, correspondingly. The packing components were distributed onto the leading structure using a delivering technique. Then, LEDs went through heat-treatment of 150 °C. Throughout this research, the optic heat characteristics of LEDs and phosphorus's number employed were compared and investigated. Figure 1(c) shows the wireframe designs for various LED structures.

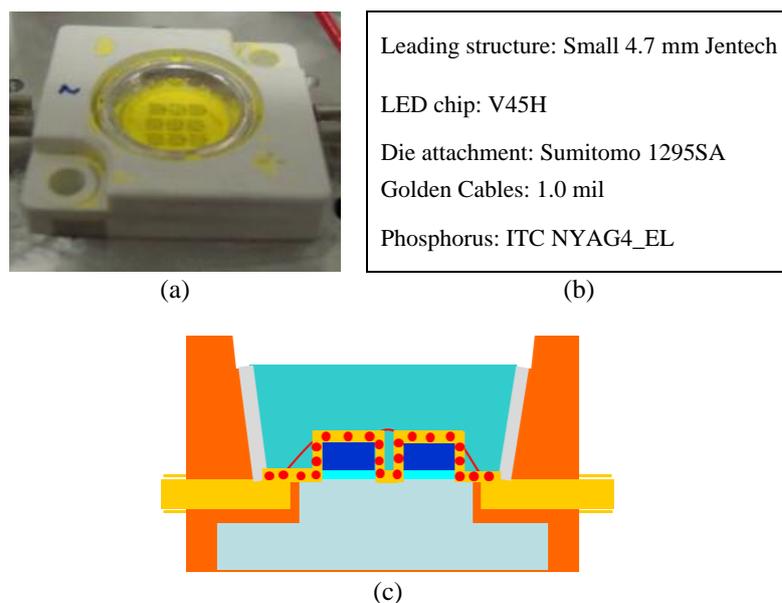


Figure 1. The phosphorus-converting MCW-LEDs as injecting  $\text{TiO}_2$ : (a) The genuine MCW-LEDs, (b) the features, and (c) MCW-LEDs structural simulation

### 3. COMPUTATION AND DISCUSSION

The luminous emissions in LEDs having conventional phosphorus and TiO<sub>2</sub>-doping phosphorus designs were 136.8 and 140.5 lm, correspondingly; the TiO<sub>2</sub>-doping phosphorus luminance emission structure was 2.7% greater than the conventional structure. The injection of TiO<sub>2</sub> (NPs) (n=2.5) accompanied by phosphorus (n=1.8), silicon (n=1.5) enhanced the median refracting indice as well as packaging components' illumination dispersion possibility, leading to an improvement. Employing a TiO<sub>2</sub>-doping phosphorus arrangement, the general reflection deficiency between the LED chips with the atmosphere was reduced, improving the LEDs' brightness efficacy. Referring to analytic results, the joint heat from conventional phosphorus and TiO<sub>2</sub>-doping phosphorus structures was 103.6 and 97.1 °C, respectively; the TiO<sub>2</sub>-doped phosphorus joint heat was 6.5 °C less than the conventional structure [25]. The decline in TiO<sub>2</sub>-doping phosphorus joint heat was due to lower illumination absorbance inside the packages and lower illuminating deficiency inside the LED's chips. TiO<sub>2</sub> doped likewise reduced the energy's level being transformed to temperature, preventing a thermal wave from forming during the packing process and thereby reducing the joint heat of the LED chips. If LED CCT variant properties are examined, angle-based CCT uniformity was defined the peak CCT subtract lowest CCT. Figure 2 shows the angle-based CCT deviations of TiO<sub>2</sub>-doping phosphorus and standard phosphorus setups. The angle-based CCT fluctuations in the conventional phosphorus and TiO<sub>2</sub>-doped phosphorus configurations were at 605 and 367 K, correspondingly, as in angular band from -70° to 70°. The TiO<sub>2</sub>-doping phosphorus arrangement displayed reduced CCT deviations than the conventional phosphorous structure, exhibiting a 39% gain. Such breakthrough was due to TiO<sub>2</sub>'s scattered ability. With the lack of TiO<sub>2</sub> doping, yellow and blue-emitting illumination is easily trapped and reflected within the package, causing insufficient chromatic fusion involving yellow and blue-emitting illumination. The uniform TiO<sub>2</sub> distribution in the phosphorus silicon encapsulating resulted in excellent diffraction, enabling consistent dispersion of the yellow and blue-emitting illumination.

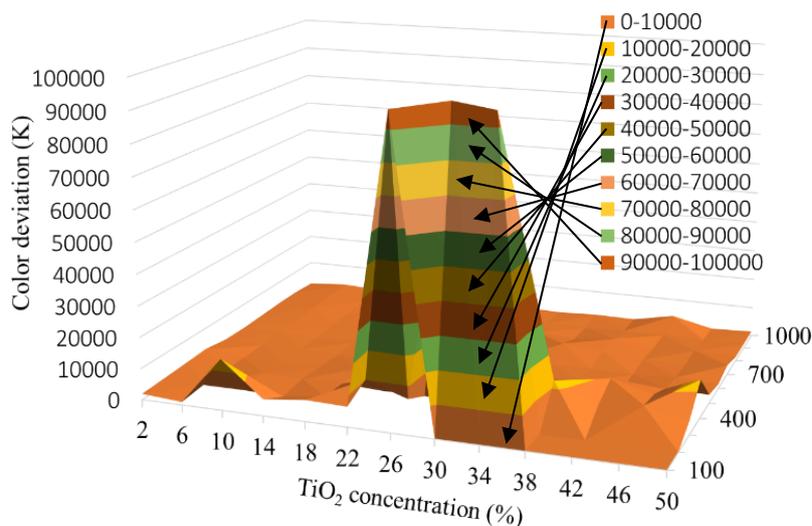


Figure 2. Phosphorus-converted MCW-LEDs chromatic deviation being the injected TiO<sub>2</sub>

The TiO<sub>2</sub>-doping phosphorus structure boosted luminous generation and angular-based CCT uniformity while lowering LED joint heat, as per the data. Additionally, the TiO<sub>2</sub>-doping phosphorus structure showed a 5% used-phosphorus reduction compared to the conventional configuration, see Figure 3. The introduction of TiO<sub>2</sub> is responsible for such deficit. TiO<sub>2</sub> possesses a great scattered ability, the phosphor silicon packaging wavelength's conversion, increasing the possibility that blue-emitting radiation overlapping the phosphorus nanoparticles and being converted into extended-wavelength illumination, improving the white LEDs dispersing features [8]. Competitive-expense TiO<sub>2</sub> doping reduces the comparably expensive phosphorous required, according to the findings. Therefore, the proposed approach improves LED efficacy while also cutting the budget of manufacturing white-emitting LEDs.

A balanced connection sphere concept was used to determine the illumination output characteristics of five packaging systems at varying source currents (a). Overview of the results of the 350 mA evaluation,

LED units I-V had illuminating yield values at 309.3, 363.8, 370.7, 378.8, 385.2 mW, correspondingly. Because the silicon lenses considerably reduce the LED chip's and silicon sheet's reflecting deficiencies, light extracted from LED II improved 17.6% over LED unit I. Because the TiO<sub>2</sub>-doping silicon lenses considerably enhance the silicone median refracting indice as well as illumination scattered efficiency, the light extracted from LED III improved 19.9% compared to LED II, reducing the LED chip's and TiO<sub>2</sub>-doping silicon lenses' dispersing deficiency. The light extracted from LED IV enhanced approximately 22.5% compared to LED I. LED IV's interior sheet was added to TiO<sub>2</sub>-doping silicon throughout most leading structure containers for a higher refracting indices as well as scattered intensity. Consequently, the overall inner reflecting of both LED chip's and silicon coating was reduced, leading to increased illumination absorption.

The lead frame cavities' exterior layer was covered in ordinary silicon for creating silicon lens that minimized the refracting indice differences among the TiO<sub>2</sub>-doped silicon or the environment, along with the internal reflecting volume. According to our results, grading arrangements with a pristine silicon filter along with a TiO<sub>2</sub>-doping silicon film would considerably reduce the reflective deficit at the LED chip-to-environment contact, leading to good illumination extraction as well as reduced inner reflection. While the appropriate TiO<sub>2</sub>-doped silicon application will improve refractive efficacy as well as illumination scattered capability, because of its diameter, the TiO<sub>2</sub>-doping silicon film transmission might be greatly diminished, impacting the LEE of LEDs implicitly and marginally. The TiO<sub>2</sub>-doped silicon layer depth must be advanced to achieve great illuminating absorption. As compared with LED IV, LED V's interior structure was composed from TiO<sub>2</sub>-doping silicon, which was used to coat the LED chip's outside for increased refracting indices with illuminating scattered efficacy, more diffusion, and a larger amount of lighting extracted. Thus, the luminous absorption efficacy of LED V grew by 24.5% than that of LED I. Additionally, when the controller power increases, so do the changes in the energy emitted by LED illumination. At a 700 mA operational voltage, the illumination emissions of LEDs I-V were 454.2, 553.0, 561.0, 570.9, 579.7 mW, correspondingly. In comparison to LED I's LEE, that of LEDs II-V grew by 21.8, 23.5, 25.7, and 27.6%, accordingly.

When the control current rises, temperature generation inside LEDs intensifies, raising the heat of the packaging components as well as LED chips. Temperature generation in LED I take a shorter duration than temperature generation in LEDs II-V because LED I contains more illumination than the rest LEDs, and thermal transfer among the LEDs and the external surroundings is decreased. The fastest increase inside LED's chip heat was driven by the highest amount of thermal production in LED I, which was accompanied by an increase in controller power. Functioning performance decreases as the temperature rises. Therefore, even though the controlling current rose, the illuminating performance of LED I fell significantly. The thermal generation volumes of LEDs were examined by examining their thermodynamic characteristics. For MCW-LED, the scattered coefficient  $\mu_{sca}$  is a primarily essential metric to determine other optical characteristics in the phosphorous composition. Premised upon the Mie-thesis, the following formulas include the scattered coefficients (SC)  $\mu_{sca}$ , the wavelengths, and TiO<sub>2</sub> ions measurement [26].

$$\mu_{sca}(\lambda) = \frac{c}{\bar{m}} \bar{C}_{sca}(\lambda) \tag{1}$$

$$\bar{C}_{sca}(\lambda) = \frac{\int^J c_{sca,D}(\lambda) f(D) dD}{\int^J f(D) dD} \tag{2}$$

$$\bar{m} = \frac{\int^J m_i(D) f(D) dD}{\int^J f(D) dD} \tag{3}$$

$$C_{sca}(\lambda) = \frac{P_{sca}(\lambda)}{I_{inc}(\lambda)} \tag{4}$$

As shown in (1)-(4) computations,  $f(D)$  represents the dimension dispersion role, while  $c$  denotes the phosphorous content (g/cm<sup>3</sup>).  $\bar{C}_{sca}(\lambda)$ ,  $C_{sca,D}$  are the scattered cross-segment and scattered cross-segment the phosphorus, correspondingly, whereas  $D$  representing the molecule dimension.  $\bar{m}$  denote the phosphor ion measurement on  $f(D)$ .  $P_{sca}(\lambda)$  displays the scattered intensity, while  $I_{inc}(\lambda)$  displays the emitting amplitude. Figure 4 shows WLED's scattered coefficients (SC) once TiO<sub>2</sub> is included. As for such a graph, TiO<sub>2</sub> diameter is a crucial component, which causes the differences in the scattered coefficients and improves colored uniformity as well. The scattered coefficients continue to rise since the phosphorus concentration rises. Such impact is far more severe at 680 nm or above wavelengths, see Figure 4(a). Despite the unit diameter of phosphorus being at 200 or 400 nm in the experiment, the scattered coefficients achieved using greater phosphorus concentration is continuously better, leading to improved chromatic uniformity. If the

phosphorus molecules' diameters are 200 or 400 nm, the SC is more stable, regardless of TiO<sub>2</sub> concentration increase, see Figure 4(b), 400 nm phosphorous ions are a great possibility to WLEDs which require increased color efficacy because of such circumstance's favorable impact upon the color quality scale (CQS). The research results suggest that WLEDs fluorescent efficiency and chromatic uniformity are assessed using both TiO<sub>2</sub> phosphorus concentration as well as phosphorus ions' diameter. These specifications could be flexibly adjusted by manufacturers, suggesting that TiO<sub>2</sub> is effective to enhance WLEDs fluorescent efficiency and chromatic uniformity.

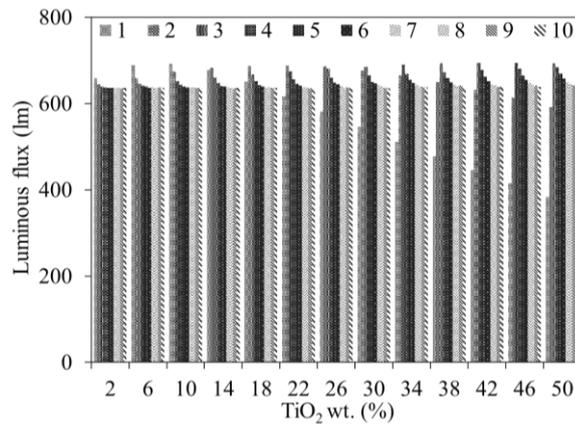
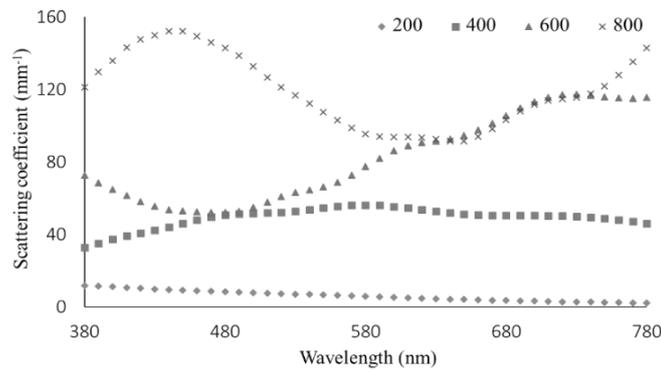
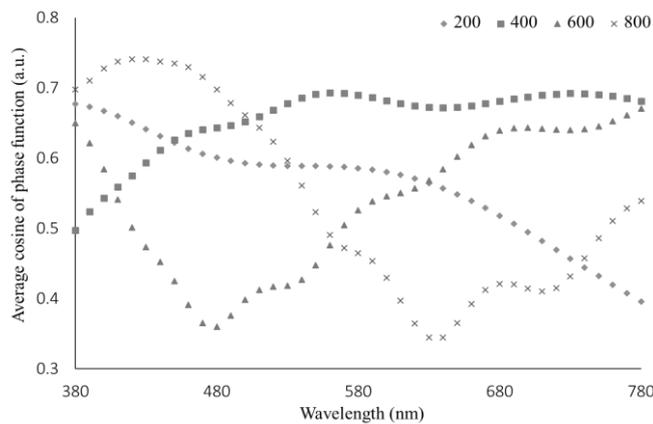


Figure 3. Phosphorus-converting MCW-LEDs luminating flux being the injected TiO<sub>2</sub>



(a)



(b)

Figure 4. Phosphorus synthesis doped TiO<sub>2</sub> ions in (a) scattered coefficients and (b) median cosine of phasing feature

#### 4. CONCLUSION

This research presents a straightforward approach of making white LEDs by altering phosphor silicone packing using TiO<sub>2</sub> NPs. The resulting arrangement has a high refracted intensity as well as illuminating scattered efficiency, decreasing illumination leakage thanks to chromatic fusion inside packages, which improves luminosity generation and CCT deviation and minimizes temperature buildup and phosphorus usage at the same time. When phosphoric silicon and TiO<sub>2</sub> are combined, the refracted indices and scattering abilities in the packaging are modified, cutting manufacturing expenses and boosting illuminating intensity, leading to an ideal LED illumination resource.

#### ACKNOWLEDGEMENTS

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**BIOGRAPHIES OF AUTHORS**

**Thanh Binh Ly**    received a Environmental Engineering Technology Master degree from the Industrial University of Ho Chi Minh City, in 2020. Currently, He is research Industrial University of Ho Chi Minh City, Vietnam. Her research interests include simulation LEDs material, renewable energy. She can be contacted at email: lythanhbinh@iuh.edu.vn.



**Nguyen Doan Quoc Anh**    was born in Khanh Hoa province, Vietnam. He has been working at the Faculty of Electrical and Electronics Engineering, Ton Duc Thang University. Quoc Anh received his PhD degree from National Kaohsiung University of Science and Technology, Taiwan in 2014. His research interest is optoelectronics. He can be contacted at email: nguyendoanquocanh@tdtu.edu.vn.



**Phan Xuan Le**    received a Ph.D. in Mechanical and Electrical Engineering from Kunming University of Science and Technology, Kunming city, Yunnan province, China. Currently, He is a lecturer at the Faculty of Engineering, Van Lang University, Ho Chi Minh City, Viet Nam. His research interests are Optoelectronics (LED), Power transmission and Automation equipment. He can be contacted at email: le.px@vlu.edu.vn.